

1SS350

Sillicon Epitaxial Schottky Barrier Diode

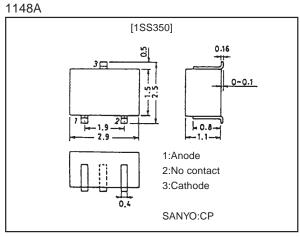
# **UHF Detector, Mixer Applications**

### Features

- · Small interterminal capacitance (C=0.69pF typ).
- · Low forward voltage ( $V_F=0.23V$  max).
- Very small-sized package permitting the 1SS350applied sets to be made small and slim.

### **Package Dimensions**

unit:mm



## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

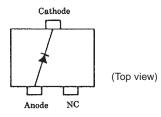
Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V <sub>RM</sub>		5	V
Forward Current	١ <sub>F</sub>		30	mA
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		-55 to +125	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	VF	I <sub>F</sub> =1mA			0.23	V
Forward Current	١ <sub>F</sub>	V <sub>F</sub> =0.5V	30			mA
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =0.5V			25	μA
Interterminal Capacitance	С	V <sub>R</sub> =0.2V, f=1MHz		0.69	0.9	pF

· Marking:BH

#### **Electrical Connection**



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